
2SD1490

Silicon NPN Epitaxial

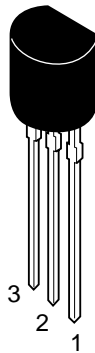
HITACHI

Application

- Low frequency power amplifier
- Complementary pair with 2SB1059

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

2SD1490

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	70	V
Collector to emitter voltage	V_{CEO}	50	V
Emitter to base voltage	V_{EBO}	6	V
Collector current	I_C	1	A
Collector power dissipation	P_C	0.75	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

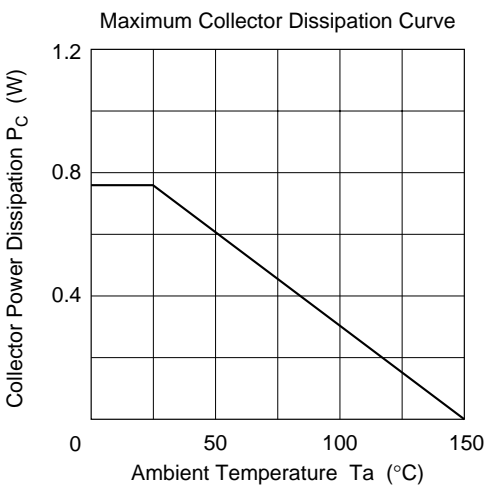
Electrical Characteristics (Ta = 25°C)

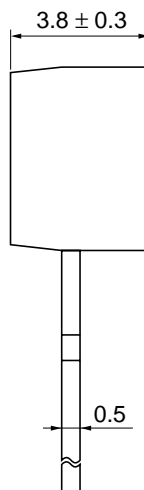
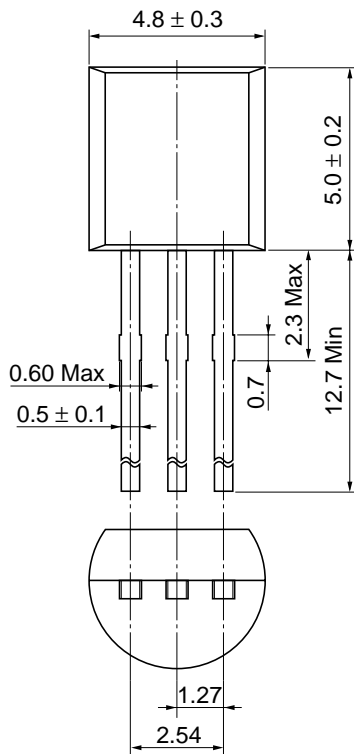
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	70	—	—	V	$I_C = 10\text{ }\mu\text{A}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	50	—	—	V	$I_C = 1\text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	6	—	—	V	$I_E = 10\text{ }\mu\text{A}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	1	μA	$V_{CB} = 80\text{ V}$, $I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	0.2	μA	$V_{EB} = 6\text{ V}$, $I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	100	—	500		$V_{CE} = 2\text{ V}$, $I_C = 0.1\text{ A}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.3	V	$I_C = 1\text{ A}$, $I_B = 0.1\text{ A}$
Gain bandwidth product	f_T	—	80	—	MHz	$V_{CE} = 2\text{ V}$, $I_C = 10\text{ mA}$
Collector output capacitance	C_{ob}	—	20	—	pF	$V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$

Note: 1. The 2SD1490 is grouped by h_{FE} as follows.

B	C	D
100 to 200	160 to 320	250 to 500

See characteristic curves of 2SD789.





Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g